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			COLLDE	Application Number	Unassigned 10 517022		
				Filing Date	October 19, 2004		
			PLICANT	First Named Inventor	Tetsuhiro et al.		
				Art Unit	Unassigned 1722		
			necessary)	Examiner Name	Unassigned Hitelines		
Sheet	1	of	1	Attorney Docket Number	93120		

	U.S. PATENT DOCUMENTS						
Examin er Initials*	Cite No.1	Document Number  Number-Kind Code <sup>2 (# known)</sup>	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear		
F.H.		4,002,523	01/11/1977	Dyer	÷		
F.H.		5,911,823	06/15/1999	Sonoda et al.	• —		

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No.1	Foreign Patent Document Country Code <sup>3</sup> -Number <sup>2</sup> -Kind Code <sup>3</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>8</sup>
F.H.		JP 63123893	05/27/1988	Shoichi et al.		Abstract
Fif.		JP 03080184	04/04/1991	NEC Corporation		Abstract
F.H.		JP 57-017494	01/29/1982	Toshiba Corporation		Abstract
FH.		JP 09-165298	06/24/1997	Koji et al.		Abstract
			1			1

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>o</sup>
БH		Murthy et al.; "Growth of Dislocation-Free Silicon Crystals in the (110) Direction for Use as Neutron Monochromators," <i>Journal of Crystal Growth</i> , Vol. 52, (1981), pp. 391-395.	
Fill.		Hoshikawa et al.; "Dislocation-Free Czochralski Silicon Crystal Growth without the Dislocation-Elimination-Necking Process," <i>Japan Journal of Applied Phys.</i> , Vol. 38 (1999) pp. L1369-L1371.	
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Examiner Signature	Littleto	Date Considered	8/2/06	
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